

36V, 20A高效异步升压转换器

36V, 20A Asynchronous Boost Converter

■ FEATURES

- Wide supply voltage operating range: 2.8V-36V
Output voltage range: up to 36V
- Built-in 40V 8mΩ Power NMOS
- Programmable switching frequency: 100K-1MHz
- Programmable switching MOSFET over current threshold: up to 20A
- Input under voltage and over temperature protection
- Packages: Pb-free Packages, ETSSOP20
- 宽输入电源范围2.8V-36V, 输出电压范围: 最高36V
- 内置40V 8mΩ功率NMOS
- 开关频率可调100K-1MHz
- 开关MOS过流阈值可调, 最高20A
- 欠压保护和过热关断保护
- 无铅封装, ETSSOP20

■ APPLICATIONS

- Bluetooth/Wi-Fi Speakers
- Chargers
- 蓝牙/ Wi-Fi音箱
- 充电
- Power Bank
- Electronic Cigarette
- 移动电源
- 电子烟
- High-power Emergency Power Supply
- 大功率应急电源

■ DESCRIPTION

The HTN865B is a high-power density, asynchronous boost converter with an 8mΩ power switch to provide a high efficiency and small size solution in portable systems.

The HTN865B has wide input voltage range from 2.8V to 36V to support different applications with different power supplies. The device has 20A switch current capability and can provide an output voltage up to 36V.

The HTN865B also implements a programmable soft-start function and an adjustable switching peak current limit function.

The HTN865B adjusts the switching frequency through an external resistor connected to the RT pin, with the switching frequency range being 100KHz-1000KHz.

The HTN865B adopts peak current mode control and an external compensation network, making the system more stable in a simpler and more flexible way.

HTN865B can be controlled to be turned on and off through EN.

HTN865B是一款高功率异步升压转换器, 集成8mΩ功率开关管, 为便携式系统提供高效的小尺寸解决方案。

HTN865B具有2.8V至36V宽输入电压范围, 可为不同应用的不同供电方式提供支持。该器件具备20A开关电流能力, 并且能够提供高达36V的输出电压。

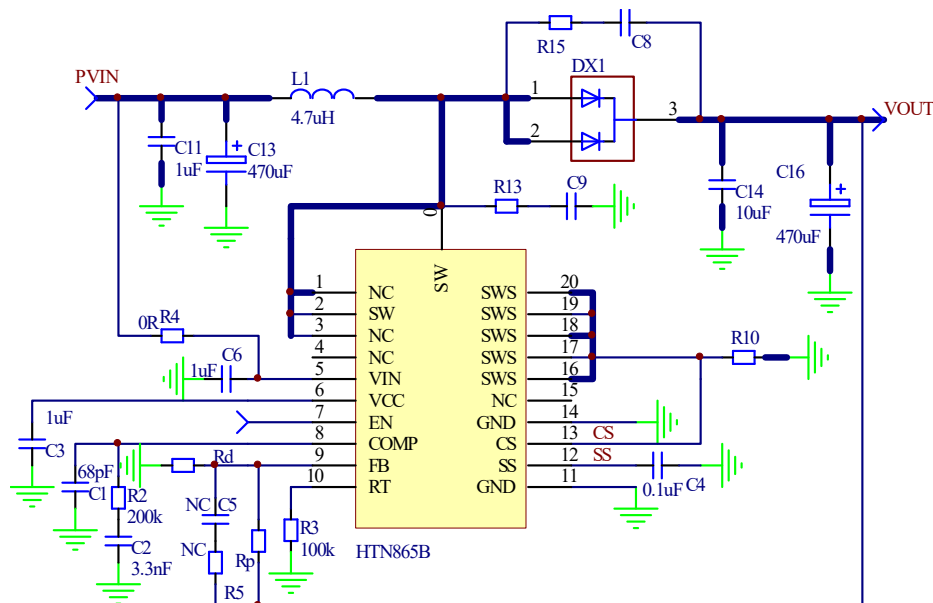
HTN865B还支持可编程的软启动, 以及可调节的开关峰值电流限制。

HTN865B通过RT管脚外接电阻调整开关频率, 开关频率范围为100KHz-1000KHz。

HTN865B采用峰值电流模式控制和外置补偿网络, 更简单更灵活的使系统稳定。

HTN865B通过EN可以控制开启和关断。

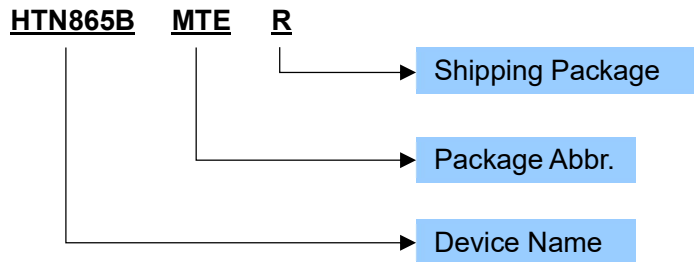
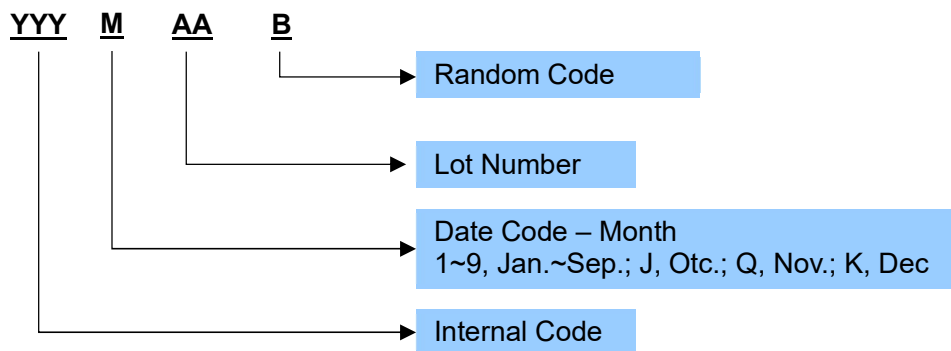
■ TYPICAL APPLICATION



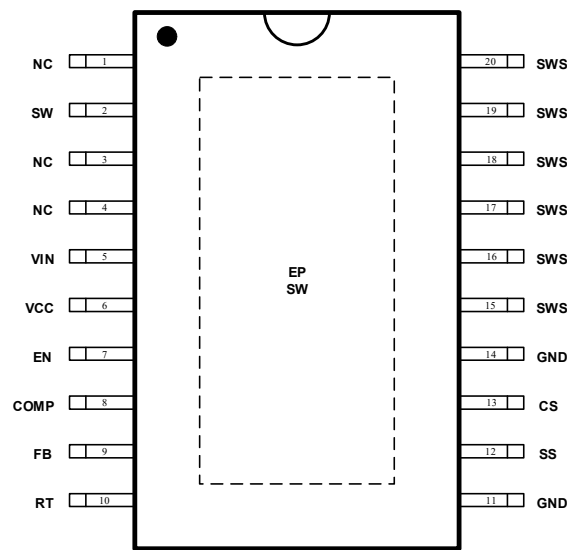
1. R13, C9; R15, C8 均做预留，用于EMI调试。
2. 若单节锂电池输入使用，VIN脚需接升压输出VOUT。
3. EN直接外加电压建议低于5V；外接高压时（如连接至PVIN），需串接R14 (>200k)。
4. Comp典型参数（**R2=200k**, C2=3.3nF, C1=100pF）可适用于大多数应用。但若输出不稳，则需调整。
5. 输出电压由FB端电阻Rp和Rd设置： $V_{OUT} = 1.2 \times \left(1 + \frac{R_p}{R_d}\right)$ ；**FB端R5, C5可不用。**
6. 开关频率FSW由RT端电阻R1设置： $FSW(kHz) \approx \frac{13465}{R1(kohm)^{0.895}}$ ，或参看典型图表；RT端悬空，则为固定200kHz。
7. SS端电容可调节软起动时间，一般可直接使用0.1uF典型值。
8. 电感峰值电流 $I_{LIM}(A) = \frac{0.1}{R10(\Omega)}$ ，**需设置一定的1.5倍以上余量**；Rilim需大尺寸封装，承受功率 $P_o > \frac{0.01}{R1(\Omega)}$ ，建议使用1812及以上封装，或多个电阻并联。
9. L选型，大多数应用可推荐10uH或22uH，额定电流建议大于ILIM设置值，并留有余量。
10. D选型，反向击穿电压建议 $> 1.5 \times V_{OUT}$ ，峰值额定电流大于ILIM设置值，且平均额定电流大于平均输出电流IOUT。

ORDERING INFORMATION

Part Number	Package Type	Package Abbr.	Eco Plan	MSL Level	Marking	Shipping Package / MOQ
HTN865BMTER	ETSSOP20	MTE	RoHS	MSL3	HTN865B YYYMAAB ¹	Tape and Reel (R) / 3000pcs

Part Number

Production Tracking Code


■ TERMINAL CONFIGURATION



Top View

■ TERMINAL FUNCTION

Terminal No.	Name	I/O ¹	Description
1,3,4	NC	-	No connection. 内部无连接
2	SW	O	Power switch Drain. 功率管漏端
5	VIN	P	Power supply for internal circuits. 芯片供电端
6	VCC	O	Output of the internal regulator. A ceramic capacitor of 1uF is required between this pin and ground. 内部整流输出, 外接1uF电容到地
7	EN	I	Enable logic input. Logic high level enables the device. Logic low level disables the device and turns it into shutdown mode. 使能输入, 高电平芯片工作; 低电平芯片进入关断状态
8	COMP	O	compensation pin 补偿管脚
9	FB	I	Feedback voltage 反馈电压
10	RT	I	Frequency Programming 频率设定
11,14	GND	G	Ground. 芯片地
12	SS	O	Soft-start programming pin. An external capacitor C _{ss} connected to ground sets the ramp rate of the internal error amplifier's reference voltage during soft-start, 100nF is usually recommended. 软启动时间设置, 接电容C _{ss} 到地, 一般建议用100nF
13	CS	I	Mosfet switch current sense MOS管开关电流检测
15,16,17,18,19,20	SWS	O	Power switch source. 功率管源端
EP	SW	O	Power switch Drain. Also provides thermal connection from the device to the board. 功率管漏端, 也是芯片散热区域

¹ I: Input; O: Output; G: Ground; P: Power; BST: BOOT Strap; OD: Open drain

■ SPECIFICATIONS¹

● Absolute Maximum Ratings²

PARAMETER	Symbol	MIN	TYP	MAX	UNIT
VIN Voltage	VIN	-0.3		42	V
SW Voltage	SW	-0.3		42	V
VCC Voltage	VCC			15	V
Maximum switching current	ILIM			20	A
Others Pin Voltage		-0.3		6	V
Moisture Sensitivity Level (MSL)			MSL3		
Ambient Operating Temperature	TA	-25		85	°C
Junction Temperature	TJ	-40		125	°C
Storage Temperature	TSTG	-40		125	°C

● Recommended Operating Conditions

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Power supply voltage	VIN		2.8		36	V
VCC Voltage	VCC			8		V
Others Pin Voltage			0		5	V
Operating Temperature Range	TA	Ambient Temperature	-25		+85	°C

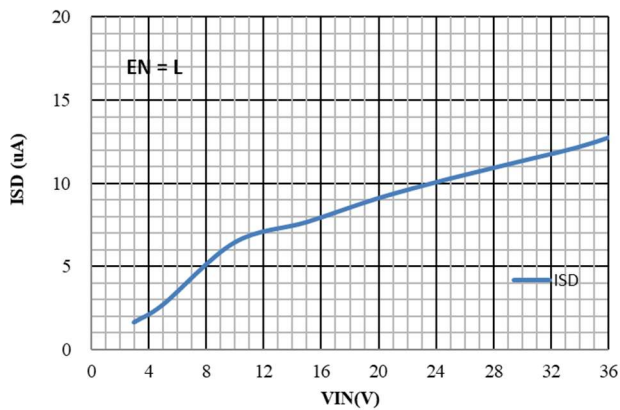
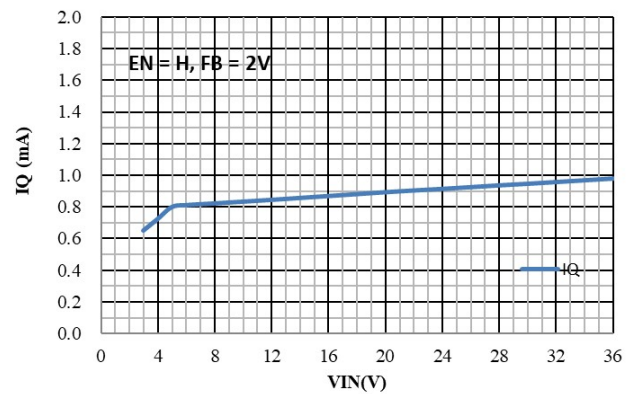
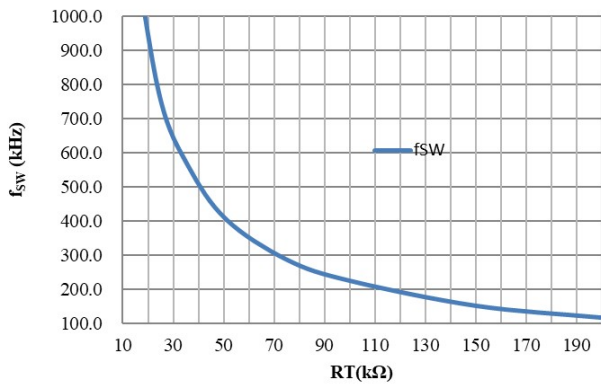
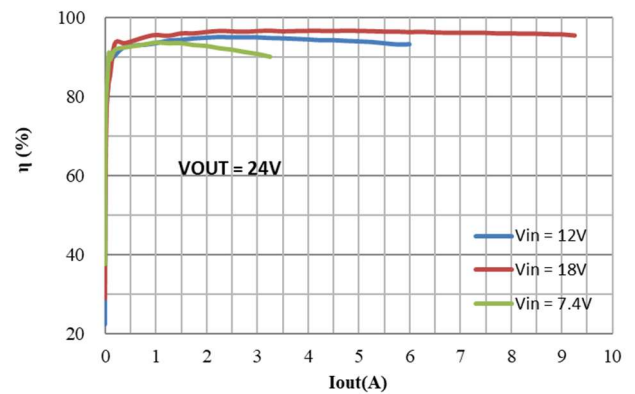
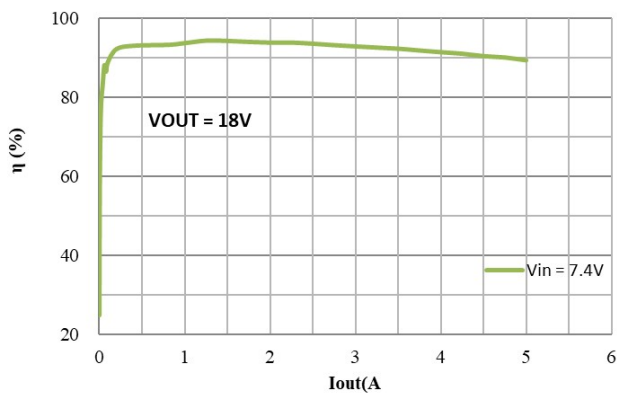
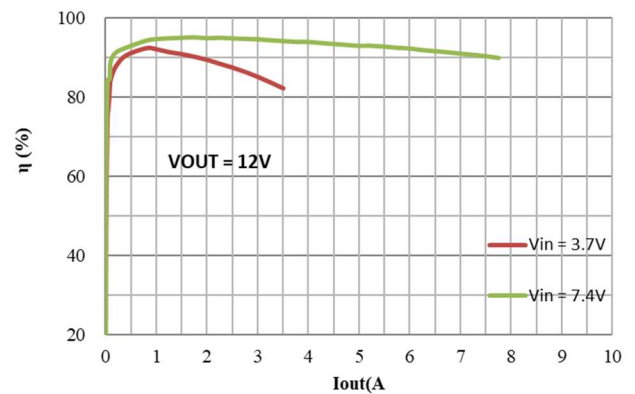
● Electrical Characteristics (VIN = 12V, TA = +25°C, unless otherwise noted.)

PARAMETER	Symbol	CONDITION	MIN	TYP	MAX	UNIT
Start-up Voltage	VIN			2.8		V
Input Supply Voltage	VIN		2.8		36	V
Under Voltage Lockout	VUVLO			2.5		V
UVLO Hysteresis				0.3		V
Average Current	ICC	FB=1.0V, Switching		1		mA
Quiescent Current	ICC	FB=1.3V, No Switching		800		uA
Shutdown Current	ICC	VEN=GND		6		uA
Input Supply Voltage	Vds			8		V
Operation Frequency	fOSC	RT=NC		200		KHz
		RT=51KΩ		400		KHz
Maximum Duty Ratio		FB=0V		93		%
Soft-Start Bias Current	ISS			2.5		uA
Feedback Voltage	VFB	HVDD=12V		1.2		V
Enable Voltage	VEN			1.24		V
Shutdown Voltage	VEN			1.12		V
Switching Current Limit	ILIM	RCS = 10mohm		10		A
MOSFET on-resistance	RDS(on)			8		mΩ
Sense Voltage	VCS			100		mV
Thermal Shutdown Threshold	TTS			160		°C
Thermal Shutdown Threshold Hysteresis	TTSH			30		°C

¹ Depending on parts and PCB layout, characteristics may be changed.

² Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

TYPICAL OPERATING CHARACTERISTICS

ISD vs VIN

IQ vs VIN

f_{SW} vs RT

I_{out} vs η

I_{out} vs η

I_{out} vs η


■ APPLICATION INFORMATION

The HTN865B is current mode boost converter. It operates with pulse width modulation (PWM). The internal resistive divider provides 1.2V reference for the error amplifier. It changes to PSM mode when the output is light load. In PSM mode, it can reduce switching loss to raise efficiency, but the output ripple is bigger.

Soft Start Function

The HTN865B has an adjustable soft start function to prevent high inrush current during start-up. To minimize the inrush current during start-up, an external capacitor, connected to the SS pin and charged with a constant current (~2.5uA), is used to slowly ramp up the internal positive input of the error amplifier. The larger the capacitance at the SS pin, the slower the ramp of the output voltage and the longer the soft-start time. A 0.1uF capacitor is usually sufficient for most applications.

Oscillator

The oscillator frequency can be set from 100KHz to 1000KHz by external resistance. Acceptable resistance values range from 220KΩ to 17KΩ. The frequency is 150KHz when the resistance is unconnected. The relationship between the timing resistance RT and frequency is shown in Figure1. The oscillator frequency can be calculated using formula below.

$$FSW(kHz) \approx \frac{13465}{R1(kohm)^{0.89}}$$

Enable Mode / Shutdown Mode

Input voltage connects to EN pin through a resistive divider to set UVLO threshold. HTN865B is enabled when EN voltage greater than 1.5V. The EN voltage is lower than 1.3V to shutdown it. In shutdown mode, the device goes into low power consumption mode. If the applications don't need to set UVLO, the EN connects to input voltage through resistance 200KΩ, and EN internal clamping circuit limit VEN is under 6V.

Current Sense Control

External switching MOSFET is turned on inductor current flows across the current sense resistor to generate VCS. VCS provides part of current mode control loop. Internal leading-edge blanking is provided to prevent premature turn off the switching MOSFET in each switching cycle.

HTN865B是电流模式升压转换器。它工作模式为脉宽调制(PWM)。内部电阻分压器为误差放大器提供1.2V参考。输出轻载时切换为PSM模式。在PSM模式下,可以减小开关损耗以提高效率,但输出纹波较大。

软启动功能

HTN865B 具有可调节软启动功能,以防止芯片启动瞬间的大电流,其通过 SS 端外接电容(CSS)实现,CSS 越大,软启动时间越长,输出电压启动越缓。0.1uF 的电容可满足大多数应用。

振荡器

振荡器频率可以通过外部电阻从 100KHz 到 1000KHz 进行设置。可接受的电阻值范围为 220KΩ to 17KΩ。不接电阻时,频率为 150KHz。时序电阻 RT 与频率的关系如图 1 所示。振荡器频率可以用下面的公式计算。

$$FSW(kHz) \approx \frac{13465}{R1(kohm)^{0.895}}$$

使能关断模式

输入电压通过电阻分压器连接到 EN 引脚,设置 UVLO 阈值。当 EN 电压大于 1.24V 时,HTN5157 使能。EN 电压低于 1.12V 关机。在关断模式下,芯片进入低功耗模式。如果应用不需要设置 UVLO,EN 通过电阻 200KΩ 连接到输入电压,EN 内部箝位电路限制 VEN 在 6V 以下。

电流检测控制

外部开关 MOSFET 打开电感电流流过电流检测电阻以产生 VCS。VCS 提供了一部分电流模式控制回路。内部前缘消隐时间内不触发过流,以防止在每个开关周期边沿误关断开关 MOSFET。

Current Limit Setting Resistor (R_{CS})

R_{CS} is connected between CS pin and ground, its calculation formula is as below. Where 0.085V is minimum threshold voltage of current sense, I_{Lp} is peak inductor current, and the factor 1.3 provides a 30% margin for tolerances.

$$R_{CS} (\Omega) = \frac{0.085V}{I_{Lp}(A) \times 1.3}$$

According to following equations calculate the peak inductor current I_{Lp}. Where I_{Lavg} is the average inductor current, I_{Lpp} is the peak-to-peak inductor current, V_{out} is the output voltage, I_{out(max)} is the output maximum current, Eff is the efficiency, F_s is the switching frequency, and the L is inductance.

$$I_{Lp} = I_{Lavg} + \frac{I_{Lpp}}{2}$$

$$I_{Lavg} = \frac{V_{out} \times I_{out(max)}}{V_{in} \times Eff}$$

$$I_{Lpp} = \frac{V_{out} - V_{in}}{F_s \times I_{out(max)}} \times \frac{Eff}{L} \times I_{Lavg}$$

Thermal Shutdown Protection

The IC will shut down automatically when the internal junction temperature exceeds +150°C. The device can restart until the junction temperature drops below +120°C approximately.

Inductor Selection

The Inductance value is decided based on different condition. 3.3μH to 47μH inductance value is recommended for general application circuit. There are three important inductor specifications, DC resistance, saturation current and core loss. Low DC resistance has better power efficiency. The inductance is calculated using formula. Where V_{out} is output voltage, F_s is switching frequency, I_{out} is output maximum current, Eff is boost efficiency and r is the ratio of the inductor peak-to-peak ripple current to the average DC inductor current at full load current. r is recommended between 0.3 and 0.5.

$$L = \left(\frac{V_{in}}{V_{out}} \right)^2 \times \frac{V_{out} - V_{in}}{F_s \times I_{out(max)}} \times \frac{Eff}{r}$$

限流电阻设置 (R_{CS})

R_{CS} 连接在 CS 引脚与地之间, 其计算公式如下: 其中 0.085V 是电流检测的最小阈值电压, I_{Lp} 是电感器的峰值电流, 因子 1.3 提供了 30% 的容差余量。

$$R_{CS} (\Omega) = \frac{0.085V}{I_L (A) \times 1.3}$$

根据下式计算电感峰值电流 I_{Lp}。其中 I_{Lavg} 为电感平均电流, I_{Lpp} 为电感峰间电流, V_{out} 为输出电压, I_{out(max)} 为输出最大电流, Eff 为效率, F_s 为开关频率, L 为电感。

$$I_{Lp} = I_{Lavg} + \frac{I_{Lpp}}{2}$$

$$I_{Lavg} = \frac{V_{out} \times I_{out(max)}}{V_{in} \times Eff}$$

$$I_{Lpp} = \frac{V_{out} - V_{in}}{F_s \times I_{out(max)}} \times \frac{Eff}{L} \times I_{Lavg}$$

热关断保护

当 IC 内部结温超过+150°C时, IC 将自动关闭, 直到结温降到+120°C以下, 芯片才能重新启动。

电感的选择

电感值是根据不同的条件来确定的。一般应用电路推荐采用 3.3μH~47μH 的电感值。有三个重要的电感规格: 直流电阻、饱和电流和铁芯损耗。直流电阻小, 功率效率高。电感用公式计算。式中 V_{out} 为输出电压, F_s 为开关频率, I_{out} 为输出最大电流, Eff 为升压效率, r 为电感峰峰纹波电流与满载时直流电感平均电流之比。r 建议在 0.3 到 0.5 之间。

$$L = \left(\frac{V_{in}}{V_{out}} \right)^2 \times \frac{V_{out} - V_{in}}{F_s \times I_{out(max)}} \times \frac{Eff}{r}$$

Capacitor Selection

Output capacitor is required to maintain the DC voltage during switching. Low ESR capacitors are preferred to reduce the output voltage ripple. Ceramic capacitor of X5R and X7R are recommended, which have low equivalent series resistance (ESR) and wider operation temperature range.

Diode Selection

Schottky diodes with fast recovery times and low forward voltages are recommended. Ensure the diode average and peak current rating exceed the average output current and peak inductor current. In addition, the diode's reverse breakdown voltage must exceed the output voltage.

Output Voltage Programming

The output voltage is set by a resistive voltage divider from the output voltage to FB. The output voltage is:

$$V_{out} = 1.2V \times \left(1 + \frac{R_p}{R_d}\right)$$

电容的选择

在开关过程中需要输出电容来维持直流电压。低 ESR 电容器是减少输出电压纹波的首选。推荐使用 X5R 和 X7R 陶瓷电容器，它们具有较低的等效串联电阻 (ESR) 和较宽的工作温度范围。

二极管的选择

建议使用恢复时间快、正向电压低的肖特基二极管。确保二极管的平均和峰值额定电流超过平均输出电流和峰值电感电流。此外，二极管的反向击穿电压必须超过输出电压。

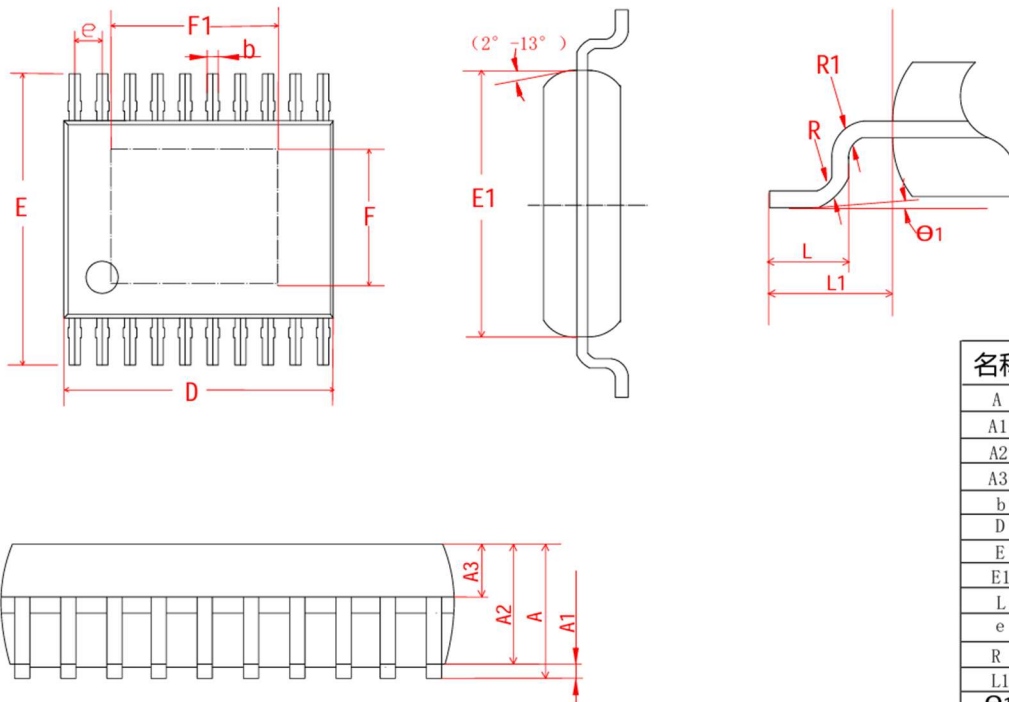
输出电压设定

输出电压由从输出电压到 FB 的电阻分压器设定。输出电压为：

$$V_{out} = 1.2V \times \left(1 + \frac{R_p}{R_d}\right)$$

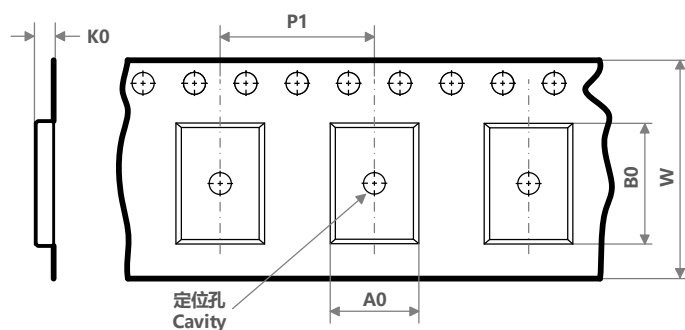
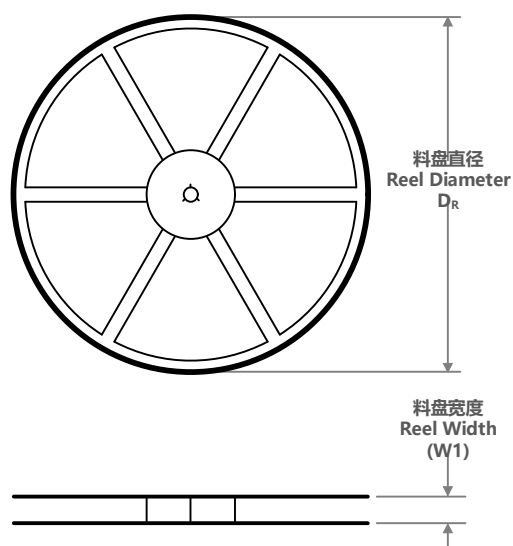
■ Revision History

Date	Version	Revision Content
2025-6-9	V0.5	Preliminary Version.

PACKAGE OUTLINE
MTE (ETSSOP20)


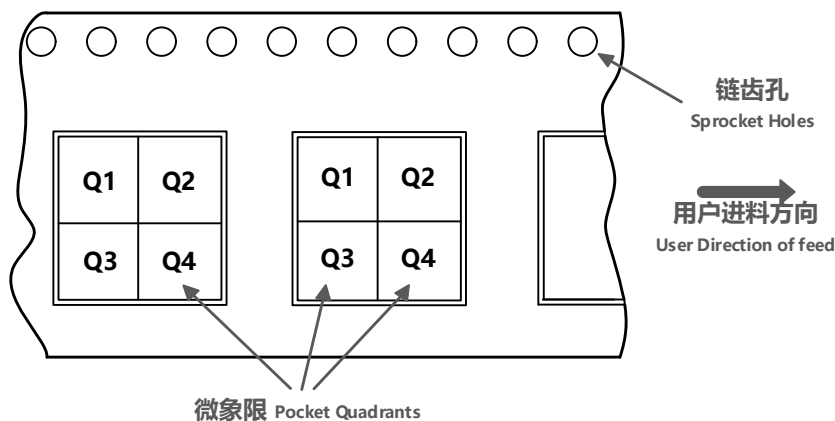
名称	尺寸		
	MIN	NOMINAL	MAX
A	1.0	—	1.10
A1	0.05	—	0.15
A2	0.90	0.95	1.0
A3	0.39	—	0.40
b	0.20	0.22	0.24
D	6.40	6.45	6.50
E	6.25	6.40	6.55
E1	—	4.35	4.40
L	0.50	0.60	0.70
e	0.65		
R	0.09		
L1	1.00REF		
$\Theta1$	0°	—	8°
F	2.99	1.00REF	3.0
F1	4.19	—	4.20

TAPE AND REEL INFORMATION

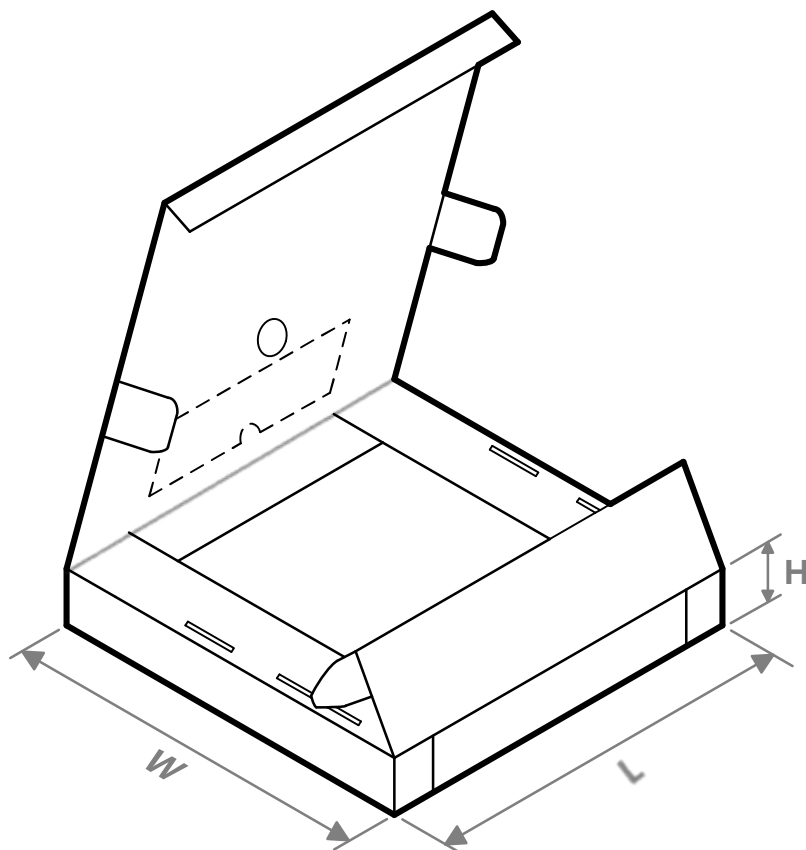


A0	Dimension designed to accommodate the component width; 料槽宽度
B0	Dimension designed to accommodate the component length; 料槽长度
K0	Dimension designed to accommodate the component thickness; 料槽厚度
W	Overall width of the carrier tape; 载带整体宽度
P1	Pitch between successive cavity centers; 相邻槽中心间距

编带 PIN1 方位象限分配 Quadrant Assignments for Pin1 Orientation in Tape



器件料号 Part No.	封装类型 Package Type	封装标识 Package Abbr.	引脚数 Pins	SPQ	料盘直径 D_R (mm)	料盘宽度 $W1$ (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 象限 Quadrant
HTN865BMTER	ETSSOP	MTE	20	3000	330	16	6.65	6.8	1.5	8	16	Q1

TAPE AND REEL BOX INFORMATION


器件料号 Part No.	封装类型 Package Type	封装标识 Package Abbr.	引脚数 Pins	SPQ	长度 Length (mm)	宽度 Width (mm)	高度 Height (mm)
HTN865BMTER	ETSSOP	MTE	20	6000	390	345	55

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